

ABSTRACT OF THE DISCLOSURE

When forming a beam shaped body by deposition using a focused ion beam device on the end of a sample, the present invention adopts a beam shaped film pattern formation method for irradiating the focused ion beam to a narrow strip shaped region from an open end of the sample to an outer space, and depositing a beam shaped film on the narrow strip shaped region, and sequentially shifting the irradiation region in a tip end direction to cause formation of a beam shaped body by growth of thin deposition layers, and causing formation of a deposition film of desired thickness on the thin deposition layers on the beam shaped body.